

PD50Y1 200G Photodiode with Integrated Lens



Ultra high-speed InGaAs/InP photodiode chip specifically designed for 200G PAM-4 applications (800GbE, 1.6TbE and 3.2TbE). This chip features an integrated backside lens and offers excellent responsivity and high speed of response in the wavelength region from 1260 nm to 1620 nm.

The integrated backside lens focuses the incoming light beam on the topside detecting area, enabling easy and efficient optical coupling by increasing the effective active diameter.

PD50Y1 is available as bare die or flip-chip mounted on a customizable carrier.

Features

- High bandwidth: 50 GHz per channel
- Easy optical coupling through integrated backside lens
- High responsivity: 0.8 A/W @ 1310 nm
- Topside pads optimized for flip-chip soldering processes using AuSn or SAC305
- Also available flip-chip soldered on ceramic carrier